

Silicon NPN transistor epitaxial type
6D978
[Applications]

Audio muting circuit

DC-DC converter

Low voltage output amplifier

[Feature]

 High DC current gain $hFE = 400 \sim 2700$

 High emitter-base breakdown voltage $BVEBO = 12V$

 Low collector saturation voltage $VCE(sat) = 0.15V$ (Typ.) at $IC/IB = 500mA/ 20mA$
[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	25	V
Collector-emitter voltage	VCEO	20	V
Emitter-base voltage	VEBO	12	V
Collector current	IC	500	mA
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	25	-	-	V	$IC = 10\mu A, IE = 0A$
Collector-emitter breakdown voltage	BVCEO	20	-	-	V	$IC = 1mA, IB = 0A$
Emitter-base breakdown voltage	BVEBO	12	-	-	V	$IE = 10\mu A, IC = 0A$
Collector cut-off current	ICBO	-	-	0.5	μA	$VCB = 25V, IE = 0A$
Emitter cut-off current	IEBO	-	-	0.5	μA	$VEB = 10V, IE = 0A$
DC current gain	hFE	400	-	2700	-	$VCE = 3V, IC = 100mA$
Collector-emitter saturation voltage	VCE(sat)	-	0.15	0.4	V	$IC = 500mA, IB = 20mA$
Transition frequency	f T	-	250	-	MHz	$VCE = 10V, IE = -50mA$
Collector output capacitance	Cob	-	7.5	-	pF	$VCB = 10V, f = 1MHz, IE = 0A$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

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